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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/804,397	03/19/2004	Sun-Jay Chang	TSM03-0695	7350
43859	7590	03/27/2006	EXAMINER	
SLATER & MATSIL, L.L.P. 17950 PRESTON ROAD, SUITE 1000 DALLAS, TX 75252			TRINH, MICHAEL MANH	
			ART UNIT	PAPER NUMBER
			2822	

DATE MAILED: 03/27/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/804,397

Applicant(s)

CHANG ET AL.

Examiner

Michael Trinh

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 06 January 2006.
2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-20 is/are pending in the application.
4a) Of the above claim(s) _____ is/are withdrawn from consideration.
5) ☐ Claim(s) _____ is/are allowed.
6) ☒ Claim(s) 1-20 is/are rejected.
7) ☐ Claim(s) _____ is/are objected to.
8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|--|---|
| 1) <input type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____ |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____ | 6) <input type="checkbox"/> Other: _____ |

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DETAILED ACTION

*** This office action is in response to Applicant's Amendment filed January 06, 2006. Claims 1-20 are pending.

*** The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.

Claim Rejections - 35 USC § 112

1. Claim 5 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Re claim 5: Base claim 1 recites "performing a third ion implant..., after removing the sacrificial spacer"; whereas, claim 5 differently recites "the third ion implant is performed before the second ion implant", wherein "...the sacrificial spacer and the first spacer acts as a mask...". However, the sacrificial spacer is already removed as in claim 1.

Claim Rejections - 35 USC § 103

2. Claims 1,4-12,15-20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Jung et al (6,335,279) taken with Peng (6,004,851) and Fulford (5,847,428).

Re claim 1, Jung teaches (at Figs 3C-3M; col 6, line 15 through col 9) a method for forming a semiconductor device comprising at least the steps of: providing a substrate having a gate electrode 116 formed thereon (Figs 3D; col 6, lines 41-49); performing a first ion implant to form region 122a-122b wherein the gate electrode 116 acts as a mask (Fig 3E, col 6, lines 50-60); forming a first spacer 124 on the substrate adjacent to the gate electrode (Fig 3F, col 6, line 61 through col 7); forming an etch stop layer 126 on the substrate (Fig 3G; col 7, lines 13-25); forming a sacrificial spacer 132 on the [second] etch stop layer 126 on the substrate adjacent to the first spacer 124 (Fig 3I; col 7, lines 13-48); performing a second ion implant wherein the sacrificial spacer and the first spacer acts as a mask; and removing the sacrificial spacer 132 (Fig 3J, col 8, lines 1-8). Re claim 12, Jung teaches (at Figs 3C-3M; col 6, line 15 through col 9) a method for forming a semiconductor device comprising at least the steps of: providing a substrate having a gate electrode 116 and a shallow trench isolation (STI) 104 formed thereon (Figs 3D; col 6, lines 41-49; lines 8-15); forming a lightly doped drain 122a-122b in the substrate adjacent to the gate electrode 116 (Fig 3E, col 6, lines 50-60); forming a

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first spacer 124 on the substrate adjacent to the gate electrode (Fig 3F, col 6, line 61 through col 7); forming an etch stop layer 126 on the substrate 100 and over the STI 104 (Fig 3G; col 7, lines 13-25); forming a sacrificial spacer 132 on the [second] etch stop layer 126 adjacent to the first spacer 124, the etch stop layer 126 preventing damage to the STI (Fig 3I, col 7, lines 13-48,44-48); performing a second ion implant wherein the sacrificial spacer and the first spacer acts as a mask; and removing the sacrificial spacer 132 (Fig 3J, col 8, lines 1-8). Re claim 4, wherein the etch stop layer 126 covers a shallow trench isolation 104 (Fig 3G; col 7, lines 13-25; and Fig 3D; col 6, lines 41-49; lines 8-15). Re claim 6, wherein the first spacer comprises a silicon nitride (col 6, line 64 through col 7, line 25). Re claims 7,19, wherein the etch stop layer 126 is an oxide (col 7, lines 13-19). Re claims 8-9,16,18, wherein the sacrificial spacer 132/128 comprises a silicon nitride (Si_3N_4) (col 7, lines 19-55), and performing an anisotropic dry etch back (col 9, lines 15-20; col 7, lines 25-36; col 1, lines 45-54). Re claims 10,20, wherein the etch stop layer 126 is an oxide formed by chemical vapor deposition techniques (col 7, lines 15-19). Re claims 11,17, wherein removing the sacrificial layer 132 is performed by an etch process using a solution of phosphoric acid (col 8, lines 1-8).

Re claims 1 and 12, Jung lacks performing a third ion implant wherein the first spacer acts as a mask; and re claims 5,15, performing a third ion implant before forming a second ion implant.

However, Peng teaches (from Fig 2e to 2h) after removing the sacrificial spacer 22a (Fig 2e, col 4, lines 25-35), performing a third ion implant to form a doped region 25 with the first spacer 21b as a mask (Fig 2h; col 4, lines 39-49). Fulford teaches (at Figs 13-15) after removing the sacrificial spacer 160, performing a third ion implant 182 to form a doped region with the first spacer 136 as a mask (Figs 15,14; col 9, line 66 through col 10, line 67), after forming second ion implantation 170. Re claim 5, Fulford also alternatively teaches (at Figs 8-12) performing a third ion implant 140 to form a doped region (Fig 8; col 8, lines 30-67) before forming a second ion implant 164 (Fig 12; col 9 lines 1-30).

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to form the semiconductor device of Jung by performing a third ion implant wherein the first spacer acts as a mask, after removing the sacrificial spacer, as taught by Peng and Fulford, by performing a third ion implanting either before or after the second ion

implanting as further taught by Fulford. This is because of the desirability to form an enhanced lightly doped region so as to reduce reverse junction leakage current and further suppress hot carrier effects, wherein the lightly doped region can be formed in the substrate by implanting ions into the substrate, as alternative, either before or after the second ion implanting.

3. Claims 2-3,13-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Jung et al (6,335,279), Peng (6,004,851) and Fulford (5,847,428), as applied to claims 1,4-12,15-20 above, taken with Bu et al (6,812,073).

The references including Jung teach (at Figs 3C-3M; col 6, line 15 through col 9) a method for forming a semiconductor device, as applied to claims 1,4-12,15-20 above.

Jung already teaches etching to form the first spacer 124 (Figs 3F-3M), but lacks forming a dielectric liner acts as an etch stop (claims 2,13), wherein exposed portions of the dielectric liner are removed after forming the first spacer (claims 3,14).

However, Bu teaches (at Figs 1B-1C) forming the first spacer 30 and forming a dielectric liner 28 (Fig 1B) on the substrate, and etching a spacer layer to form the first spacer 30 wherein the dielectric liner 30 acts as an etch stop (col 4, lines 17-27; col 3, line 58 through col 4, lines 54).

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to form the semiconductor device of Jung by further forming a dielectric liner on the substrate and acting an etch stop during etching to form the first spacer, as taught by Bu. This is because of the desirability to protect the underlying layers, and to prevent significant effect and damage to other layers during etching to form the first spacer.

Response to Amendment

4. Applicant's arguments with respect to pending claims 1-20 have been considered but they are not persuasive, and are moot in view of the new ground(s) of rejection.

** Applicant remarked about Peng that "...It should be noted that spacer 21b is formed after removing the sacrificial spacer 22a,...It should also be noted that because the first spacer is formed after removing the sacrificial spacer, Peng does not disclose the step 'performing a second ion implant where the sacrificial spacer and the first spacer acts as a mask...'"

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In response, this is noted and found unconvincing. First, as clearly shown in Figures 2(e) of Peng, the L-shaped first spacer 21a and the sacrificial spacer 22a acts as a mask during the step of performing a second ion implant to form a doped region 12 in the substrate 10. Although the L-shaped first spacer 21a in Figure 2e is modified, after removing the sacrificial spacer 22a, to have a differently shaped first spacer, not L-shaped first spacer 21b, it is still the first spacer.

Additionally, Fulford also teaches (at Figs 13-15) after removing the sacrificial spacer 160, performing a third ion implant 182 to form a doped region with the first spacer 136 as a mask (Figs 15,14; col 9, line 66 through col 10, line 67), after forming second ion implantation 170.

The rejections are outstanding and maintained.

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

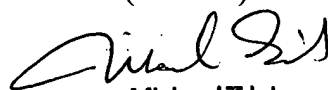
A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Michael M. Trinh whose telephone number is (571) 272-1847. The examiner can normally be reached on M-F: 9:00 Am to 5:30 Pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Zandra Smith can be reached on (571) 272-2429. The central fax phone number is (703) 872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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Michael Trinh
Primary Examiner